

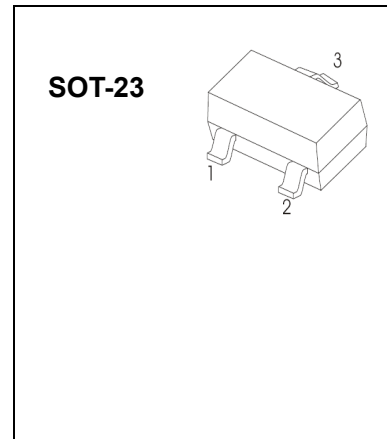
## SOT-23 Plastic-Encapsulate Transistors

**BC856**

**BC857**

**BC858**

**FEATURES**



**MAXIMUM RATINGS (Ta=25°C unless otherwise noted)**

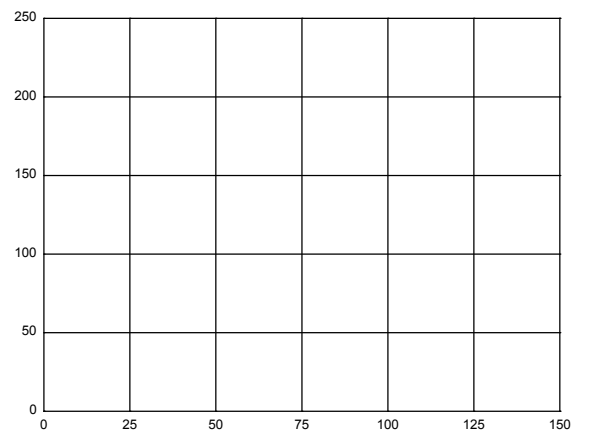
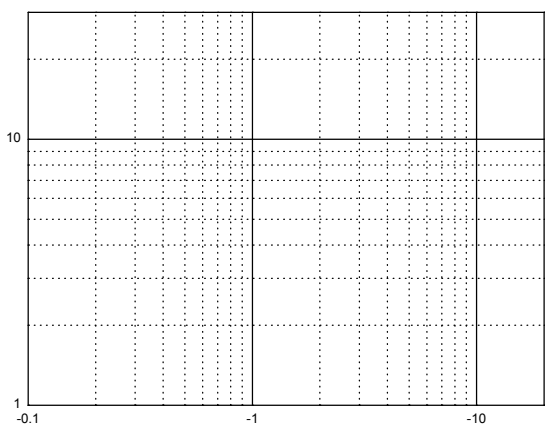
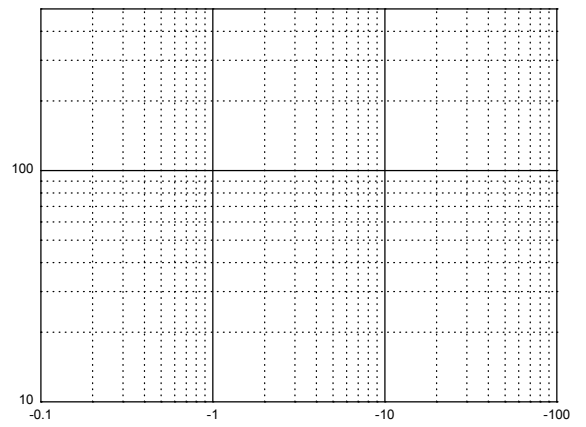
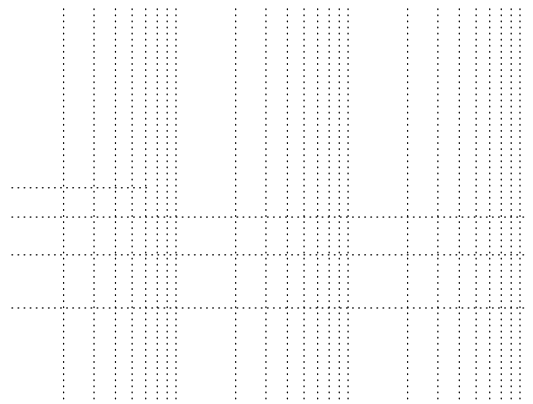
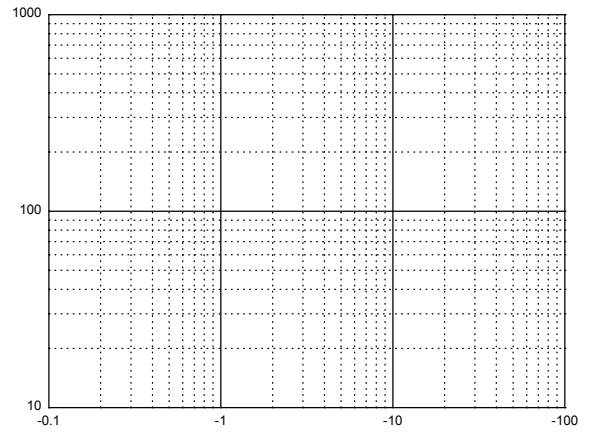
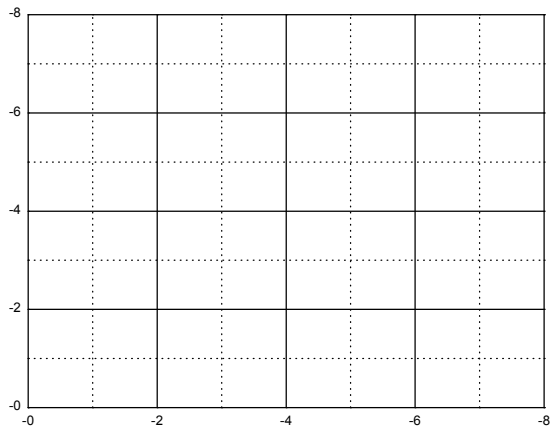
Symbol	Parameter	Value	Unit
V <sub>CB0</sub>			
V <sub>CEO</sub>			
V <sub>EBO</sub>		-5	V
I <sub>C</sub>			
P <sub>C</sub>			mW
R <sub>JA</sub>	Thermal Resistance From Junction To Ambient		°C/W
T <sub>J</sub>			°C
T <sub>stg</sub>		-65 +150	°C

**DEVICE MARKING**

BC856A=3A;BC856B=3B;  
 BC857A=3E;BC857B=3F;BC857C=3G;  
 BC858A=3J; BC858B=3K; BC858C=3L

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage BC856 BC857 BC858		μ			
Collector-emitter breakdown voltage BC856 BC857 BC858					
Emitter-base breakdown voltage		μ			
Collector cut-off current BC856 BC857 BC858					μ
Emitter cut-off current					μ
DC current gain BC856A, 857A,858A BC856B, 857B,858B BC857C,BC858C					
Collector-emitter saturation voltage					
Base-emitter saturation voltage					
Transition frequency					
Collector capacitance					



Note:  
1. Controlling dim

—  
2000  
1  
—1000  
—500